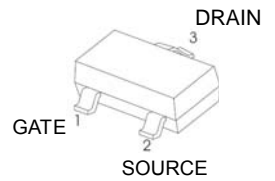
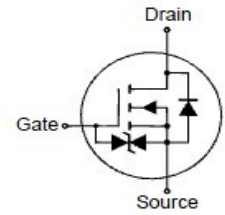




### BSS138K Plastic-Encapsulate MOSFETS

N-Channel 50-V(D-S) MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
50V	3.5Ω@10V	220mA
	6Ω@4.5V	



#### FEATURE

High density cell design for extremely low  $R_{DS(on)}$   
Rugged and Reliable

#### APPLICATION

Direct Logic-Level Interface: TTL/CMOS  
Drivers: Relays, Solenoids, Lamps, Hammers; Display,  
Memories, Transistors, etc.  
Battery Operated Systems  
Solid-State Relays

**SOT-23**

**MARKING : SS**

#### Maximum ratings ( $T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	50	V
Continuous Gate-Source Voltage	$V_{GSS}$	±20	
Continuous Drain Current	$I_D$	0.22	A
Power Dissipation	$P_D$	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^{\circ}C/W$
Operating Temperature	$T_j$	150	$^{\circ}C$
Storage Temperature	$T_{stg}$	-55 ~+150	



$T_a=25^{\circ}\text{C}$  unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	50			V
Gate-body leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$			$\pm 5000$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$			0.5	$\mu A$
		$V_{DS} = 30V, V_{GS} = 0V$			100	nA
<b>On characteristics</b>						
Gate-threshold voltage (note 1)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 0.25mA$	0.80		1.50	V
Static drain-source on-resistance (note 1)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.22A$			3.50	$\Omega$
		$V_{GS} = 4.5V, I_D = 0.22A$			6	
Forward transconductance (note 1)	$g_{FS}$	$V_{DS} = 10V, I_D = 0.22A$	0.12			S
<b>Dynamic characteristics (note 2)</b>						
Input capacitance	$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$		27		pF
Output capacitance	$C_{oss}$			13		
Reverse transfer capacitance	$C_{rss}$			6		
<b>Switching characteristics</b>						
Turn-on delay time (note 1,2)	$t_{d(on)}$	$V_{DD} = 30V, V_{DS} = 10V, I_D = 0.29A, R_{GEN} = 6\Omega$			5	ns
Rise time (note 1,2)	$t_r$				18	
Turn-off delay time (note 1,2)	$t_{d(off)}$				36	
Fall time (note 1,2)	$t_f$				14	
<b>Drain-source body diode characteristics</b>						
Body diode forward voltage (note 1)	$V_{SD}$	$I_S = 0.44A, V_{GS} = 0V$			1.4	V

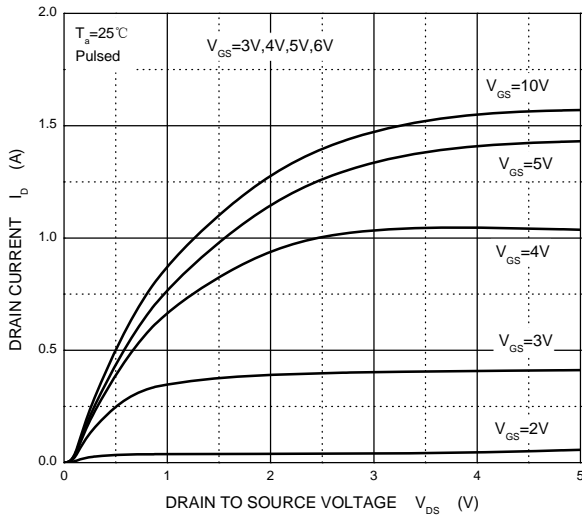
**Notes:**

1. Pulse Test ; Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
2. These parameters have no way to verify.

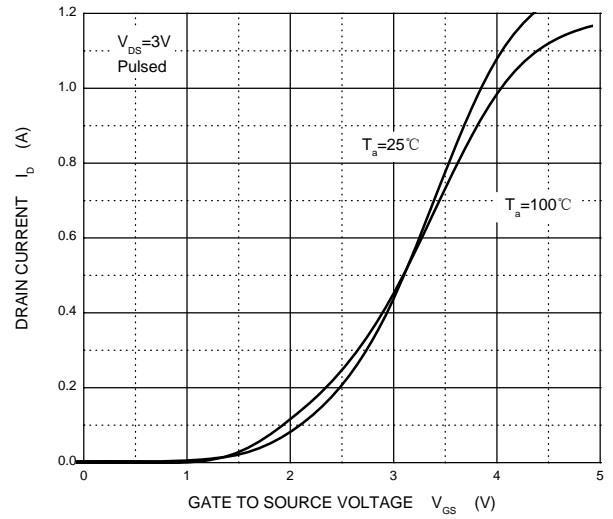


## Typical Characteristics

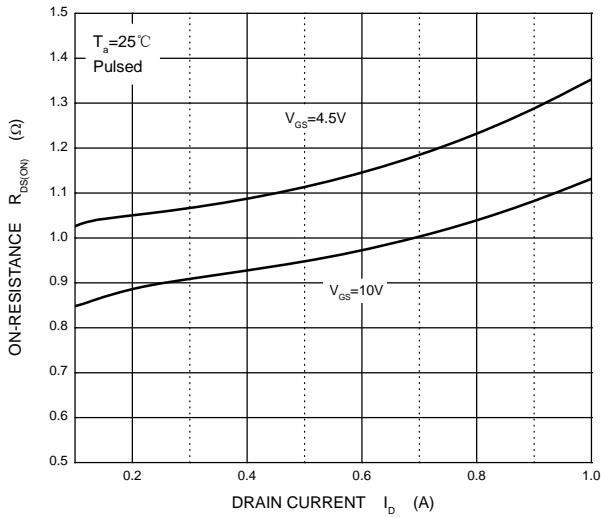
### Output Characteristics



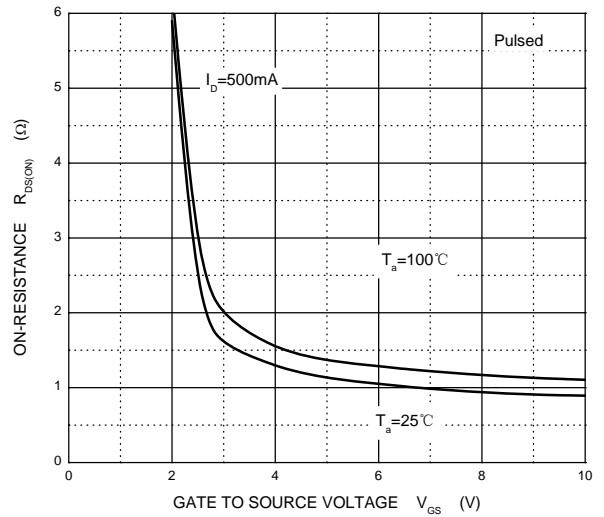
### Transfer Characteristics



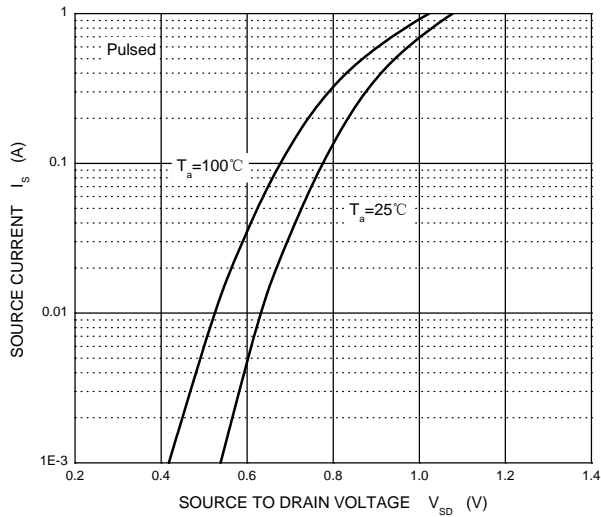
### $R_{DS(ON)}$ — $I_D$



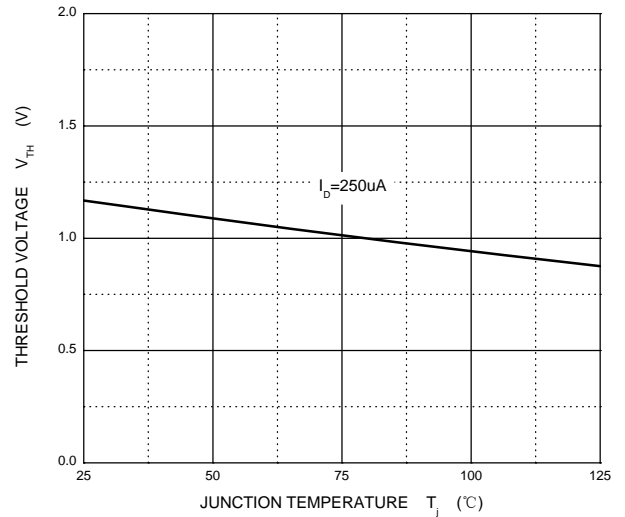
### $R_{DS(ON)}$ — $V_{GS}$



### $I_S$ — $V_{SD}$



### Threshold Voltage

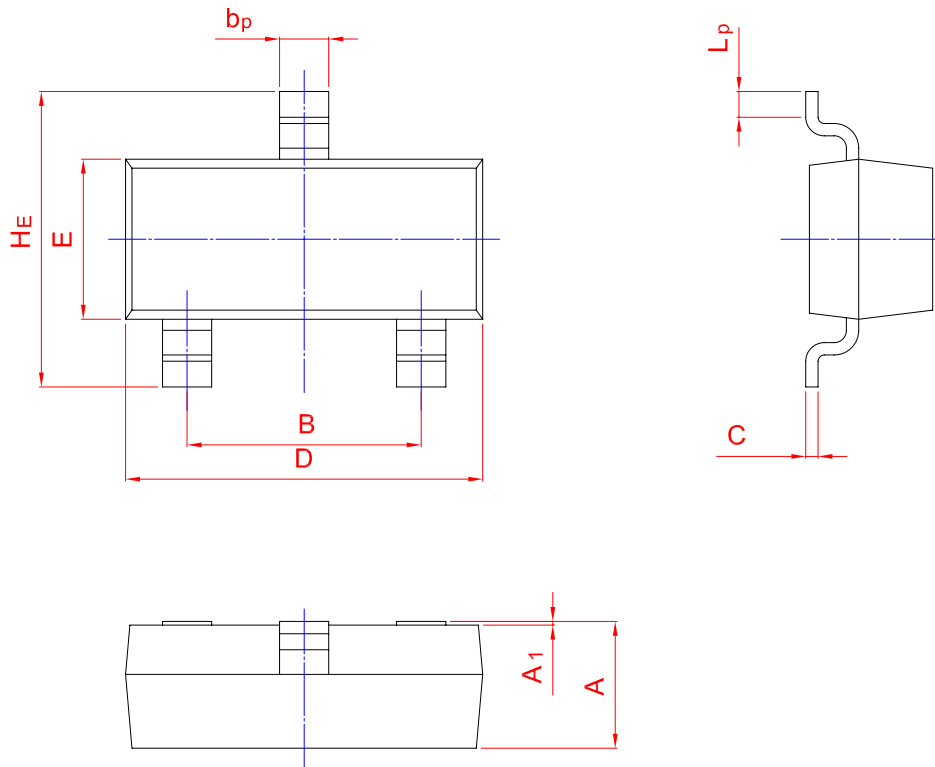
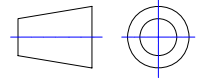




## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20